

METHOD OF REMOVING ETCH RESIDUES

Abstract of the Disclosure

Organic etch residues are often left within vias formed by etching through resist masks. Since the etch is designed to expose an underlying metal layer and is directional in order to produce vertical via sidewalls, the residue often incorporates metal. The present invention discloses a method of removing such etch residues while passivating exposed metal, including exposing the residue to ammonia. In the disclosed embodiment, ammonia and oxygen are mixed in a plasma step, such that the resist can be burned off at the same time as the residue treatment. The residue can thus be easily rinsed away.

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